

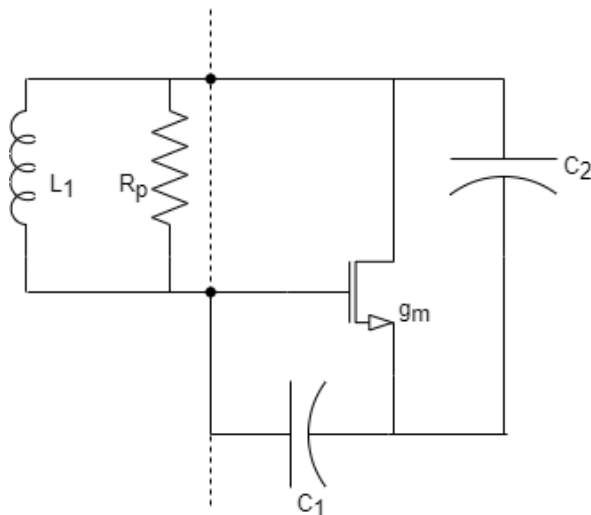
# EE 619

## Radio Frequency Microelectronic Chip Design

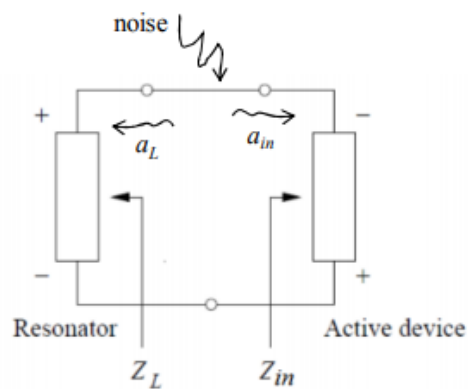
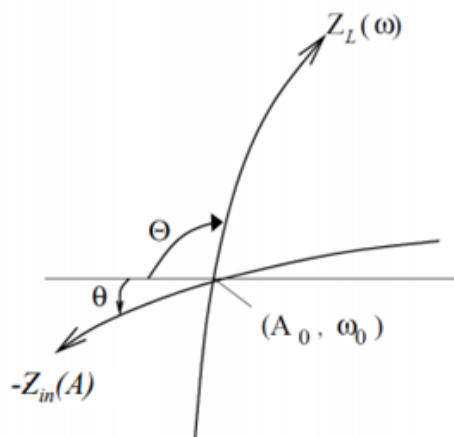
### Endsem Exam

4<sup>th</sup> May 2021, 3.00pm-6.00pm

1. For the given collpits oscillator, prove that the condition of oscillation is  $g_m \cdot R_p = 4$  and  $C_1 = C_2$  (3 M)

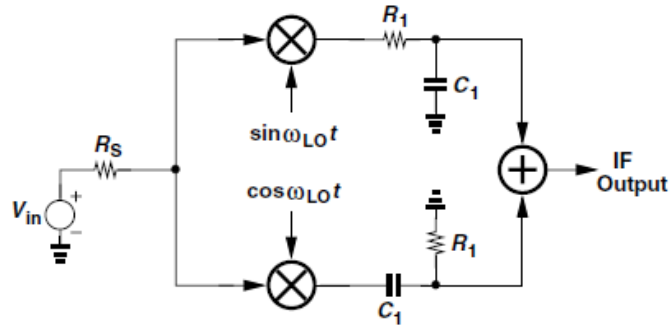


2. For oscillation stability prove that  $\Theta + \Theta$  is between 0 and 180 degree. (3 M)

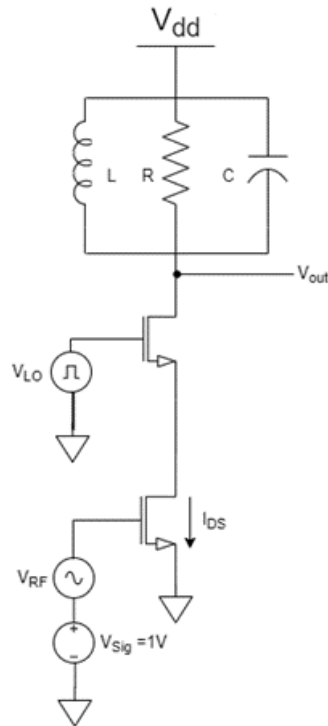


**Model of Oscillator**

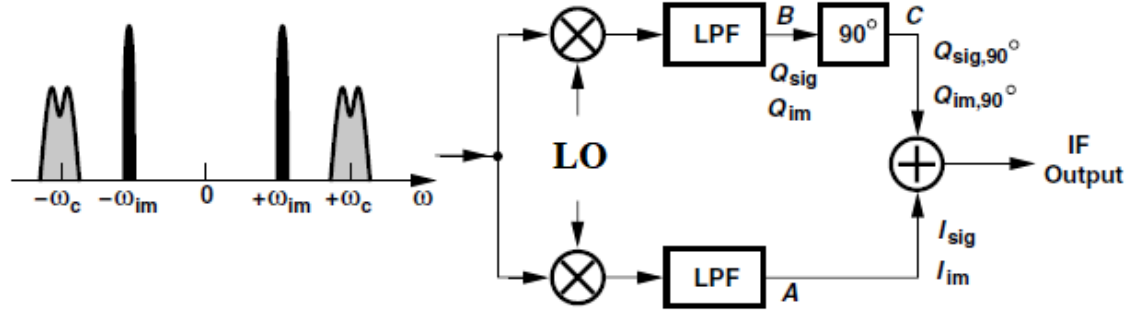
3. The simplified Hartely architecture shown incorporates mixers having a voltage conversion gain of  $A_{\text{mix}}$  and infinite input impedance. Taking into account only the noise of the two resistors, compute the noise figure of the receiver with respect to a source resistance of  $R_S$  at an IF of  $1/R_1 C_1$ . **(3 M)**



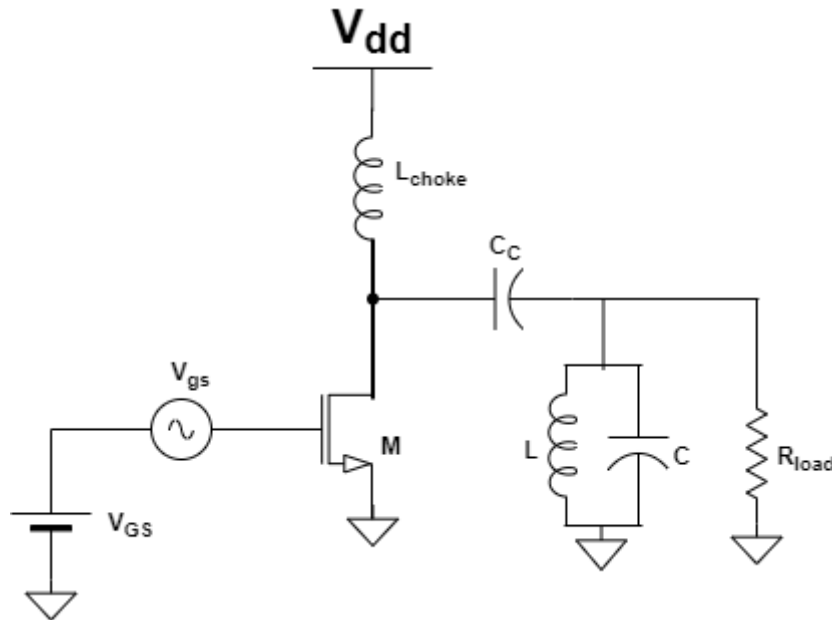
4. In the given figure, find the voltage conversion gain ( $A_{VC}$ ) of the mixer in dB. Assume that the resonant tank circuit (LRC) will sufficiently allow the  $(\omega_{RF} - \omega_{LO})$  frequency component and reject others. Given,  $g_m$  of the MOSFETS is  $2\text{mS}$ ,  $R=3\text{K}\Omega$ ,  $V_{\text{bias}}=1\text{V}$ ,  $V_{\text{thn}}=0.5\text{V}$ , Amplitude of the square wave of LO= $1.2\text{V}$ , (LO oscillated between 0 and 1.2 with frequency  $\omega_{LO}$ ). (Assume  $V_{DD} = 1.2\text{V}$ ) **(3 M)**



5. For the given architecture, derive the expression of **Image Rejection Ratio (IRR)** as a function of  $\epsilon$  and  $\Delta\theta$ . Hence prove that  $IRR \approx \frac{4}{\epsilon^2 + \Delta\theta^2}$  if  $\Delta\theta \ll 1\text{rad}$  and  $\epsilon \ll 1\text{rad}$ . (Assume one LO waveform is expressed as  $\sin\omega_{LO}t$  and the other as  $(1+\epsilon)\cos(\omega_{LO}t + \Delta\theta)$  due to mismatches)
- (4 M)**



6. Design a class-B RF power amplifier to deliver an output power of 5.1dBm at  $f_0=2.45\text{GHz}$ . The bandwidth is 500MHz. Assume  $V_{DD}=1.8\text{V}$ ,  $V_{th}=0.6\text{V}$  (Threshold voltage of NMOS)  $\mu_n C_{ox}=200\mu\text{A/V}^2$ . (Assume input AC source  $v_{gs}=0.2\cos(\omega t)$ ). Tabulate the values of  $R_{load}$ ,  $L$ ,  $C$ ,  $W/L$  of transistor  $M$ . Draw the voltage waveform at  $R_{load}$  and current waveform  $I_d$  of transistor  $M$  of at least one cycle. Clearly label the amplitudes.
- (6 M)**



7. A Hilbert transform of a signal  $m(t) \leftrightarrow m_h(t)$  with the relation (2 M)

$m_h(t) = \frac{1}{\pi} \int_{-\infty}^{+\infty} \frac{m(\tau)}{t-\tau} d\tau$  and  $M_H(f) = -j \operatorname{sgn}(f) \cdot M(f)$  show that for a upper sideband modulated signal resulting from  $m(t)$  and  $\cos(2\pi f_c t)$  is given by  $s(t) = \frac{1}{2} [m(t)\cos(2\pi f_c t) - m_h(t)\sin(2\pi f_c t)]$

8. The below figure shows the concept of Heterodyne Transmitter. Signal conversion happens in two steps as shown. The frequency of up-conversion is  $f_0 = 5\text{GHz}$ . Units in spectrum are in MHz. Assume that  $f_1 = 1\text{GHz}$  and  $f_2 = 4\text{GHz}$ . The spectrum of I signal is real. The Q spectrum is 90 degrees phase shifted version of I spectrum (Imaginary). The I and Q signals are at base band (Close to DC). Our goal is to have final PA transmitter spectrum at 5GHz.

- Draw the 3D spectrum at A, B, C, and D (4M)
- Sketch the characteristics of the desired BPF? (Center frequency & Stopband) (2M)

